

25.1) Using **SPICE** simulations, show the effects of clock feedthrough on the voltage across the load capacitor for the switch circuits shown in Fig 25.40. How does this voltage change if the capacitor value is increased to 100fF?

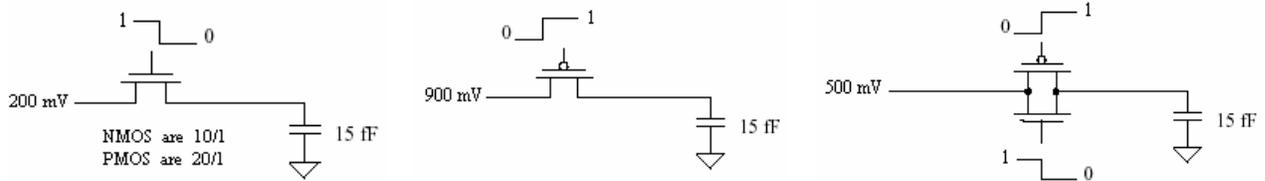
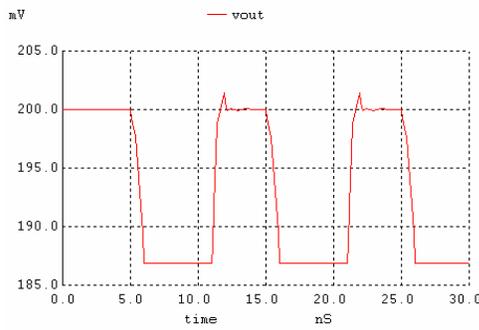


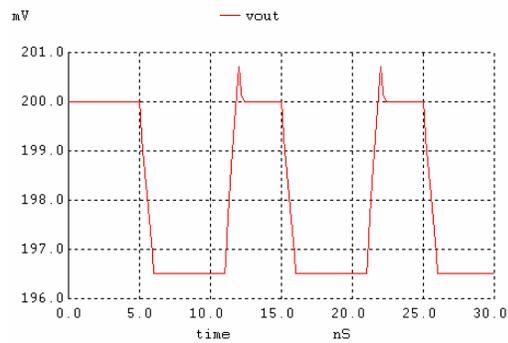
Fig 25.40

The simulations to follow show the clock feedthrough on each of the switch circuits shown (above) with the two different cap sizes.

Sim showing clock feedthrough across cap for C = 15fF & 100fF with 200 mV applied:

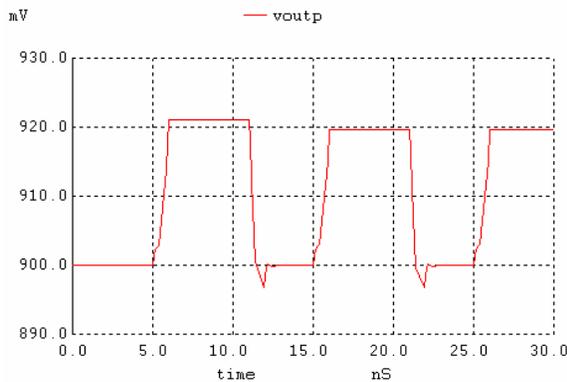


C = 15fF

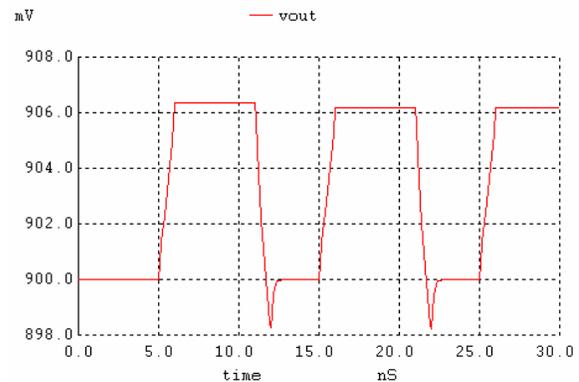


C = 100fF

Sim showing clock feedthrough across cap for C = 15fF & 100fF with 900 mV applied:



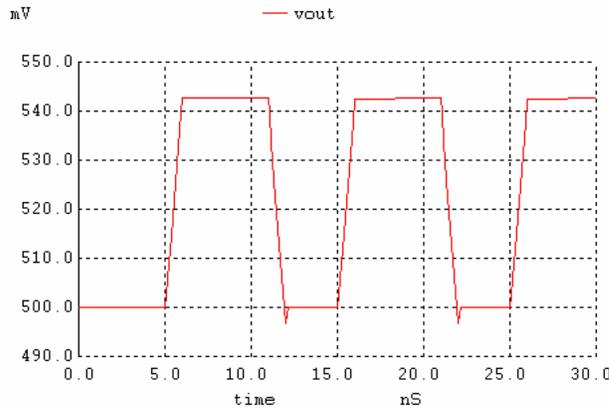
C = 15fF



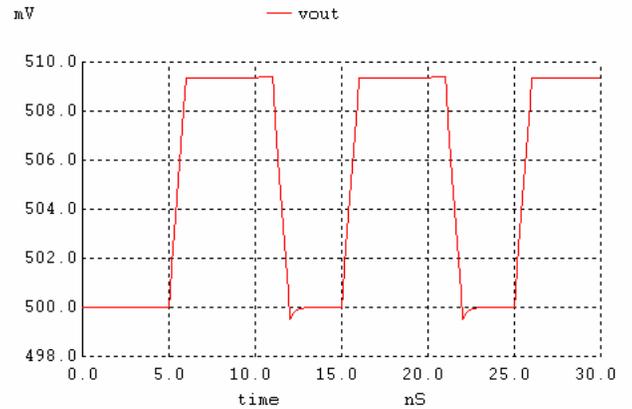
C = 100fF

25.1) cont'd

Sim showing clock feedthrough across cap for C = 15fF & 100fF with 500 mV applied:



C = 15fF



C = 100fF

If the capacitor is increased to 100fF the voltage change across the capacitor is decreased and voltage comes closer to the applied voltage. The result is due to the voltage change experienced between the switch's overlap capacitance and 100fF is less significant than for the 15fF cap.

Netlist

```
.control
destroy all
run
plot vout
.endc

.tran 1n 30n
.options scale=50n

vinp    vinp    0      DC      .2
Vphi1   phi1    0      DC      0      PULSE 1 0.5n 0 0.5n 10n
Vphi2   phi2    0      DC      0      PULSE 0 1.5n 0 0.5n 10n

*M1     vinp    phi1    vout    0      NMOS L=1 W=10
M2     vinp    phi2    vout    VDD    PMOS L=1 W=20

C1     vout    0      15fF
*C2     vout    0      100f
*50nm BSIM4 models
```

Prob 25.2: Repeat (1) if dummy switches are used. Show schematics of how the dummy switches are added to the schematics.

[Ans]: Simulations w/ half-sized dummy switch attached to output (drain) of the transistor are shown below.

Fig 25.2-1 Clock Feedthrough Dummy switches schematics

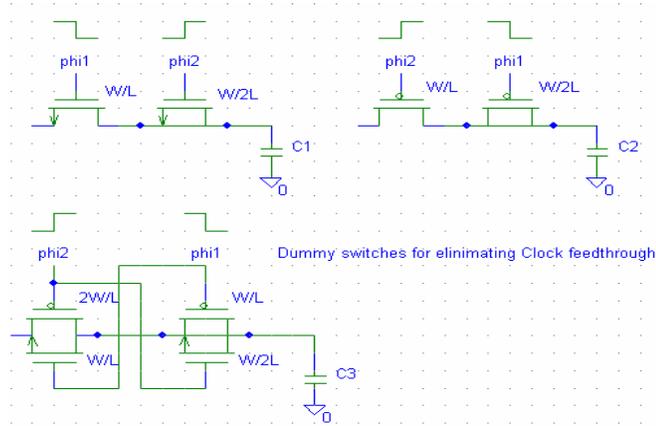


Fig 25.2-2 Clock Feedthrough performance simulation on NMOS, PMOS, and TG With Dummy switches (left) w/o (right)

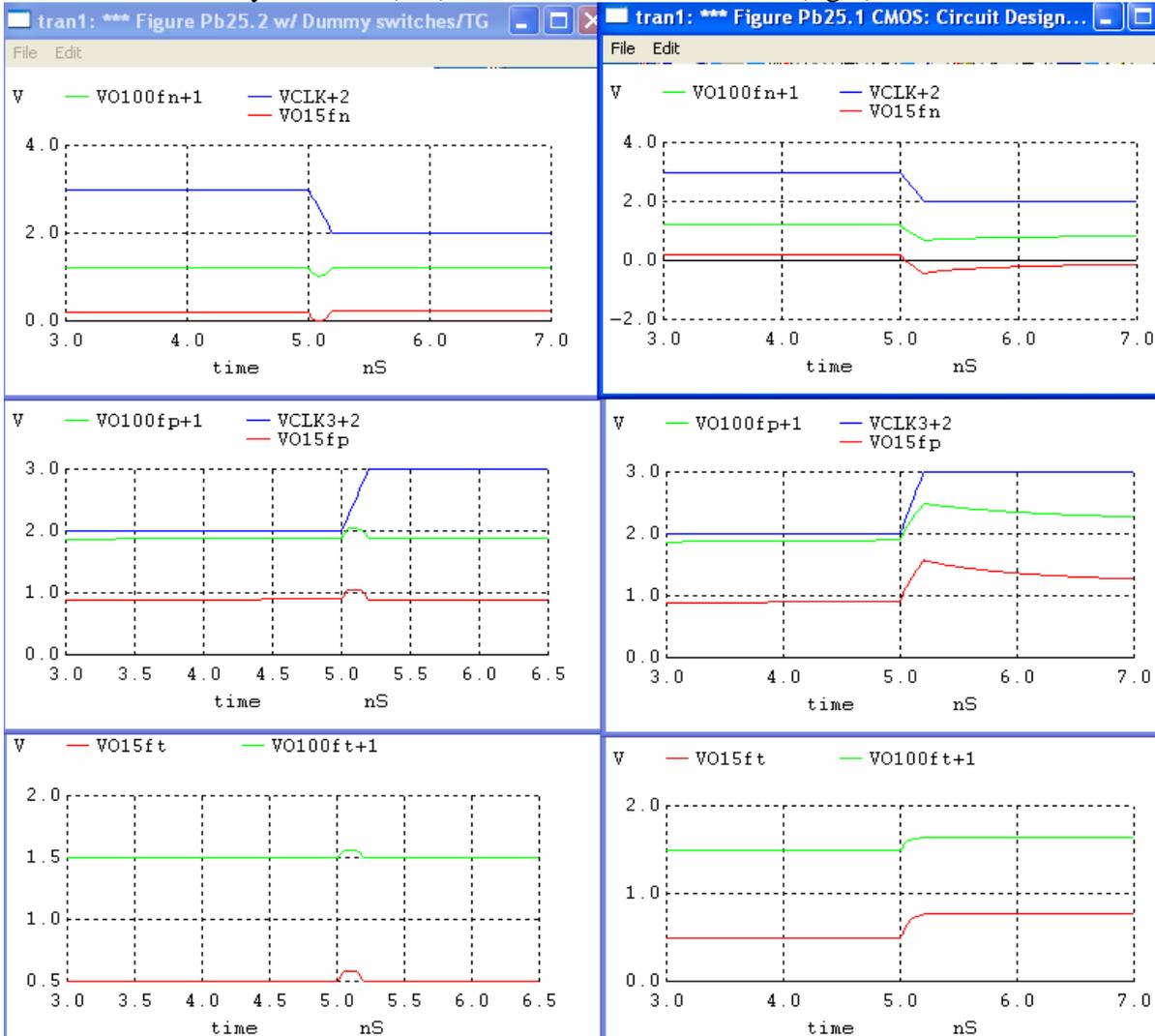
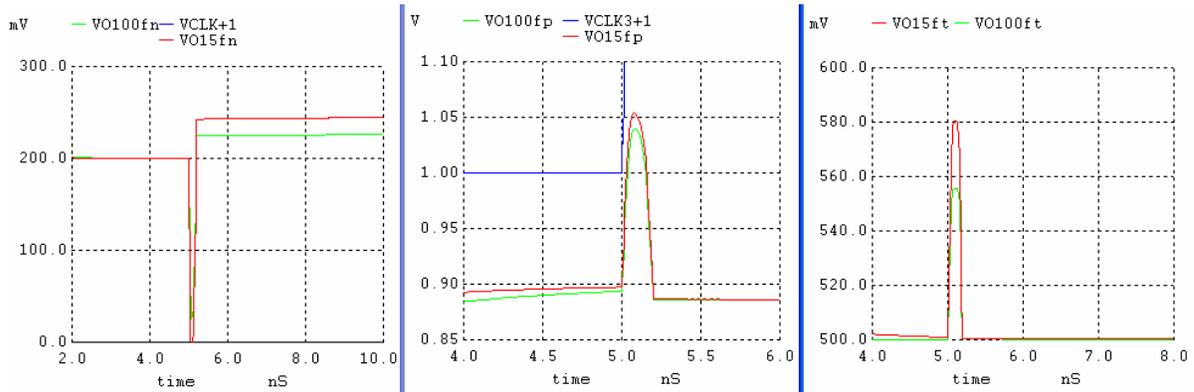


Fig 25.2-2 Clock Feedthrough performance on NMOS, PMOS, and TG
w/ CL=50fF (red), 100fF (green)



Conclusion:

1. Clock Feedthrough results from voltage divider C_{gd} and C_{load} . The larger CL is, the less voltage drops on CL. Therefore, better immune to clock Feedthrough.
2. TG gate has much less clock feedthrough than either PMOS or NMOS switch in both cases of w/ and w/o dummy compensation.
3. Pulse width equals to clock rising or falling time in practical means imperfect switching.

SPICE *** Figure Pb25.2 w/ Dummy switches/TG

```
.control
destroy all

run
plot VO15fn VO100fn VCLK+1
plot VO15fp VO100fp VCLK3+1
plot VO15ft VO100ft
.endc

.option scale=1u
.TRAN 20p 20n 0.5n UIC
VDD VDD 0 1

***** Nswitch ****
VIN VIN 0 0.2
VCLK VCLK 0 PULSE(1 0 5NS 0.2NS 0.2NS 20NS 100NS)
VCLK3 VCLK3 0 PULSE(0 1 5NS 0.2NS 0.2NS 20NS 100NS)

VCLK2 VCLK2 0 PULSE(1 0 5NS 0.2NS 0.2NS 20NS 100NS)
VCLK4 VCLK4 0 PULSE(0 1 5NS 0.2NS 0.2NS 20NS 100NS)

MN1 VO15fn VCLK VIN 0 NMOS L=1 W=10
MND1 VO15fn VCLK3 VO15fn 0 NMOS L=1 W=5
CL VO15fn 0 15f IC=0

MN2 VO100fn VCLK2 VIN 0 NMOS L=1 W=10
MND2 VO100fn VCLK4 VO100fn 0 NMOS L=1 W=5
CL2 VO100fn 0 100f IC=0

***** Pswitch ****
VIP VIP 0 0.9
MP1 VO15fp VCLK3 VIP VDD PMOS L=1 W=20
MPD1 VO15fp VCLK VO15fp VDD PMOS L=1 W=10
```

```

CL3      VO15fp  0      15f      IC=0

MP2      VO100fp VCLK4  VIP      VDD      PMOS L=1 W=20
MPD2     VO100fp VCLK2  VO100fp VDD      PMOS L=1 W=10
CL4      VO100fp 0      100f     IC=0

***** TG *****
VI       VI      0      0.5
VCLKTP  VCLKTP  0      DC 1 PULSE(0 1 5NS 0.2NS 0.2NS 20NS 100NS)
VCLKTN  VCLKTN  0      DC 1 PULSE(1 0 5NS 0.2NS 0.2NS 20NS 100NS)
CL5      VO15ft  0      15f      IC=0
XTG15   VDD     VCLKTP VCLKTN  VI      VO15ft  TG
XTGD15  VDD     VCLKTP VCLKTN  VO15ft  TGDUM

VI100   VI100  0      0.5
VCLKTP2 VCLKTP2 0      DC 1 PULSE(0 1 5NS 0.2NS 0.2NS 20NS 100NS)
VCLKTN2 VCLKTN2 0      DC 1 PULSE(1 0 5NS 0.2NS 0.2NS 20NS 100NS)
CL6      VO100ft 0      100f     IC=0
XTG100  VDD     VCLKTP2 VCLKTN2  VI100  VO100ft TG
XTGD100 VDD     VCLKTP2 VCLKTN2  VO100ft TGDUM

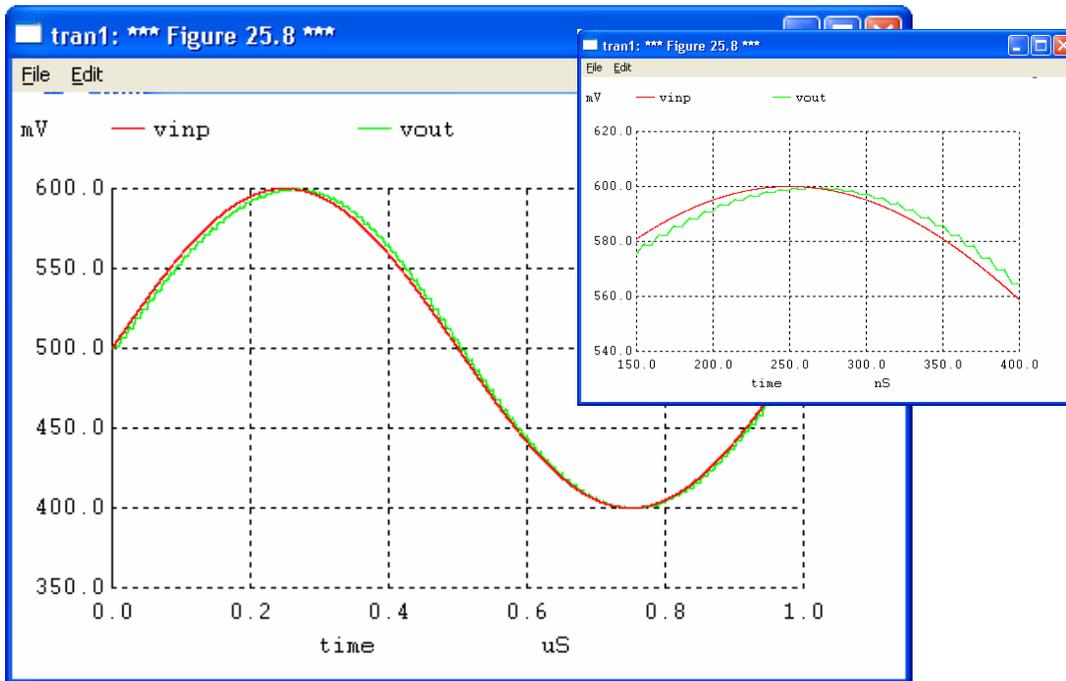
.subckt  TG      VDD      pg      ng      in      out
M1      out     pg      in      VDD     PMOS L=1 W=20
M2      out     ng      in      0       NMOS L=1 W=10
.ends

.subckt  TGDUM  VDD      pg      ng      io
M1      io      ng      io      VDD     PMOS L=1 W=10
M2      io      pg      io      0       NMOS L=1 W=5
.ends

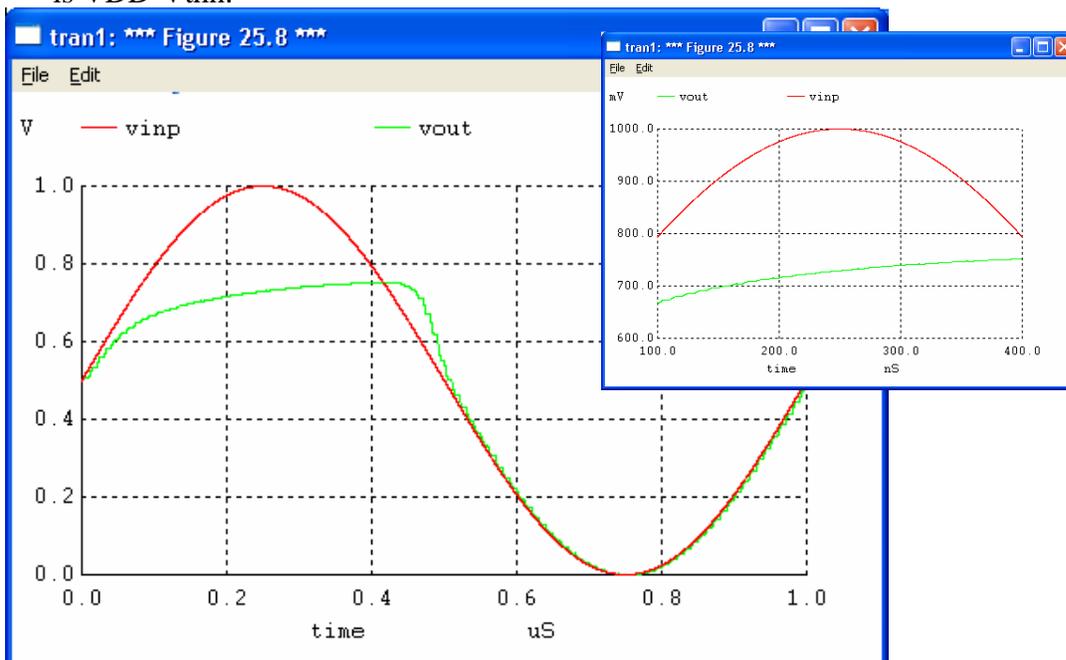
```

25.3) Using a voltage controlled voltage source for the op-amp with an open-loop gain of 10^6 use SPICE to show how the track-and-hold seen in Fig. 25.8 operates with a sinewave input. What happens if the input sinewaves's amplitude is above $V_{DD}-V_{thn}$? Use a 100MHz clock (strobe) pulse with a 50% duty cycle and an input sinewave frequency of 5MHz. Note the input sinewave should be centered around $V_{cm}(=500mV)$.

First we'll show the operation of the track-and-hold with an input sinewave amplitude below $V_{DD}-V_{thn}$.



The second part of the problem asked for an input sinewave above $V_{DD}-V_{thn}$. From the graphs we can see that the output voltage gets clipped, this is due to the strobe pulse, input of the NMOS gate, only going to 1V so the max voltage passed through the NMOS is $V_{DD}-V_{thn}$.



*** Figure 25.8 ***

```
.control  
destroy all  
run  
plot vinp vout  
.endc
```

```
.tran 100p 1000n  
.options scale=50n
```

```
* clock signals
```

```
Vphi1 phi1 0 DC 0 PULSE 1 0 5n 0 0 5n 10n
```

```
* input signals
```

```
*vinp vinp 0 DC 0 SIN 500m 100m 1MEG
```

```
vinp vinp 0 DC 0 SIN 500m 500m 1MEG
```

```
* op-amp model
```

```
E1 vout 0 vp vout 1e6
```

```
* capacitors
```

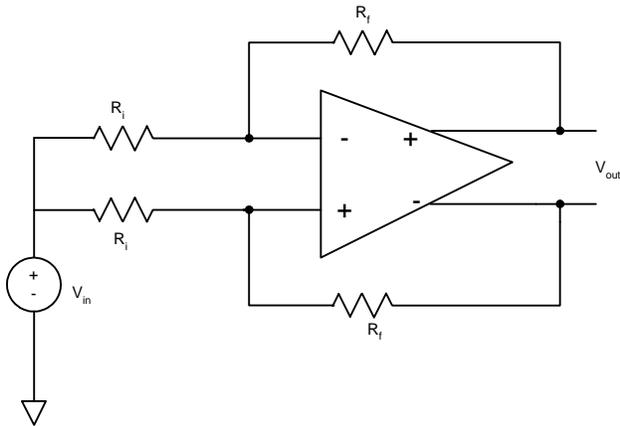
```
Ch vp 0 1p
```

```
* MOSFET switches
```

```
M1 vinp phi1 vp 0 NMOS L=1 W=10
```

```
* 50nm BSIM4 models
```

25.4) The simple differential topology is shown in the figure below:



The netlist for the above figure is shown below:

*** Question 25.4 ***

```
.control
destroy all
run
plot vp+0.1 vm
plot vop+0.1 vom-0.1 vcm
.endc
```

```
*.DC Vin 0.0 1.0 0.01
.tran 10n 0.1n
.options scale=50n
```

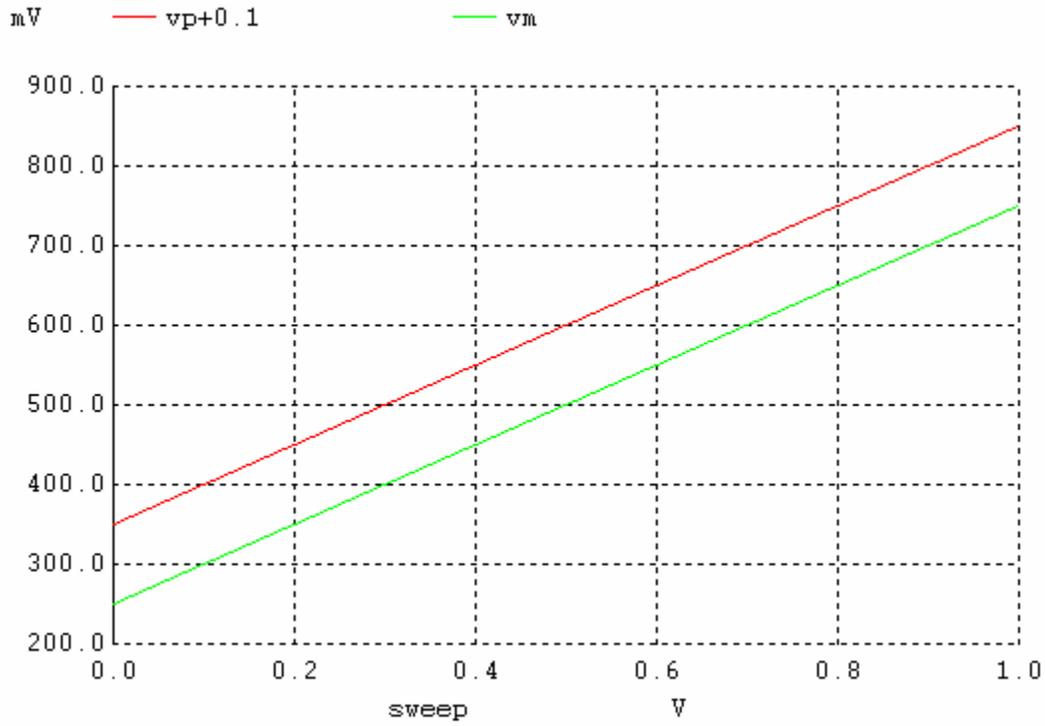
```
* input signals
Vin inp 0 DC 0.1
```

```
* op-amp model
E1 vop vcm vp vm 1e6
E2 vcm vom vp vm 1e6
Vcm vcm 0 DC 500m
```

```
*Feedback Resistors
Rfm vop vm 10k
Rfp vom vp 10k
```

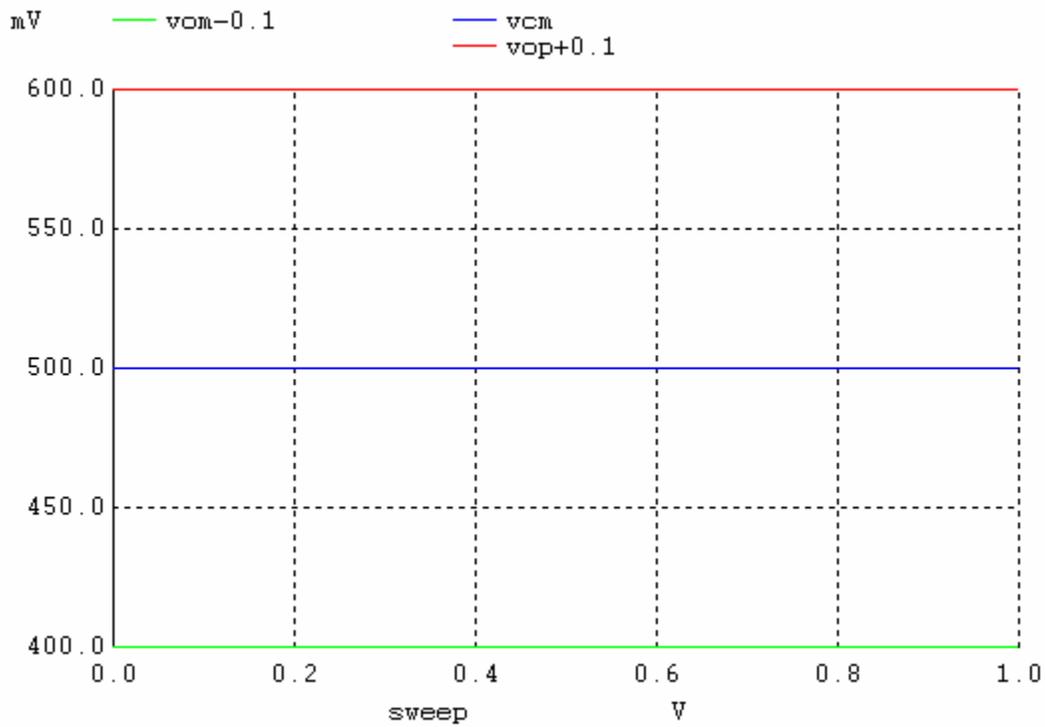
```
*Input Resistors
Rim vm inp 10k
Rip vp inp 10k
```

When V_{in} is swept, the output looks like the following:



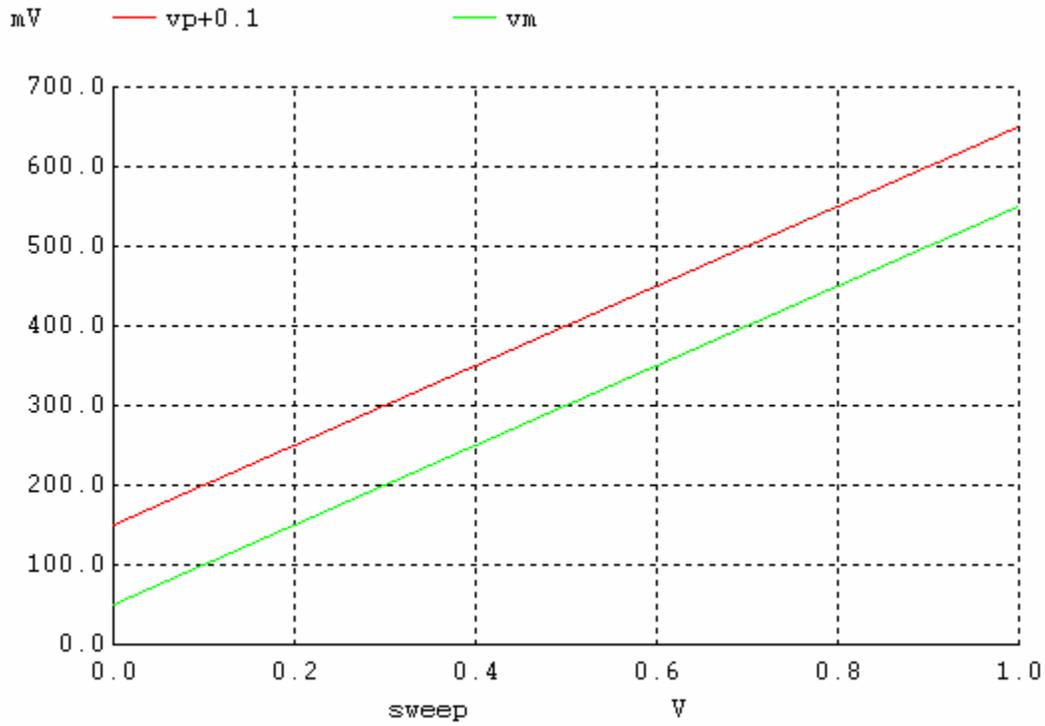
The input terminals are equal at all voltages.

The output of the differential amplifier is:



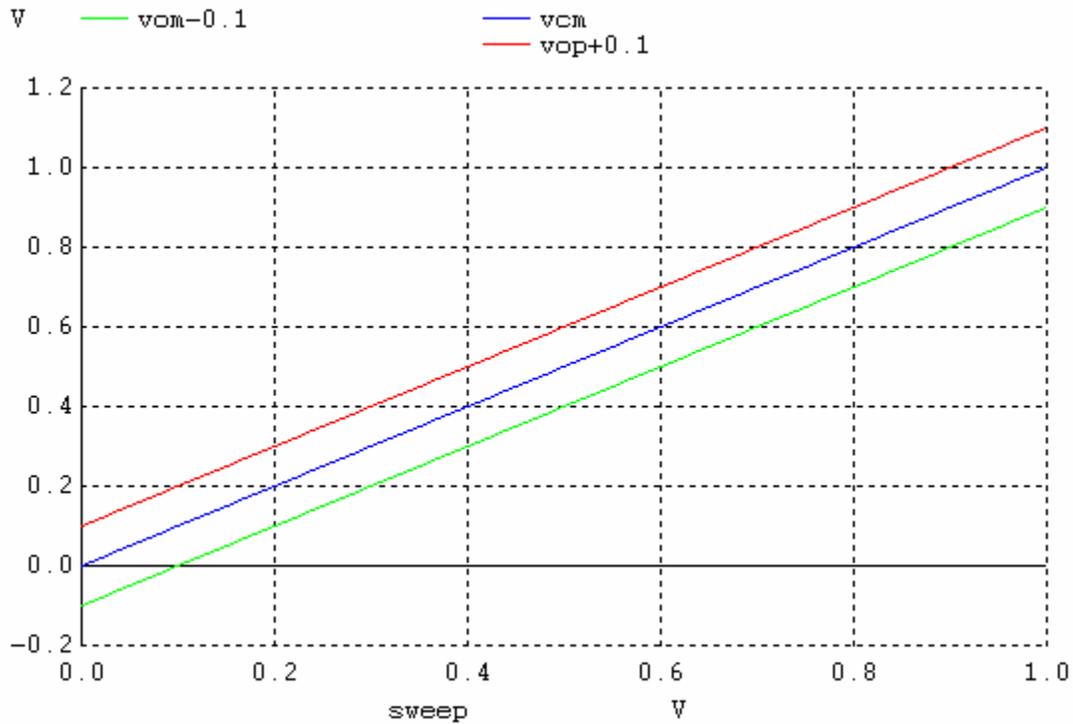
Note that the output is exactly at the common mode voltage.

When V_{cm} is swept:



Note that once again that the input terminals though varying are still the same.

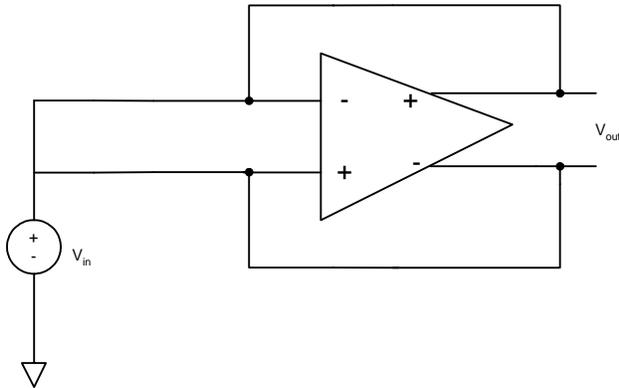
The output of the differential amplifier is shown below:



Once again it should be noted that though the output voltages are different, they are still equal to the common mode voltage.

This is to be expected since the output always referenced to the common mode voltage and not ground. Thus, since the gain of the voltage controlled voltage sources are high, they change the input voltages such that the output is always at the common mode voltage. The currents flowing through the resistors maybe different but it will not be possible to setup a situation such that the output common voltage is not the same as what was defined in the SPICE circuit model.

Note however, that a circuit like the following will cause the output voltage not to be at the common mode:



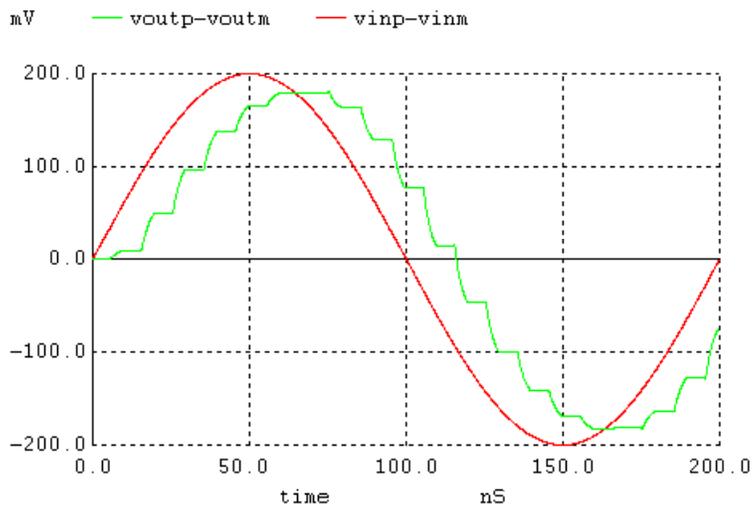
However this is unpractical and will cause simulation problems.

Problem 25.5

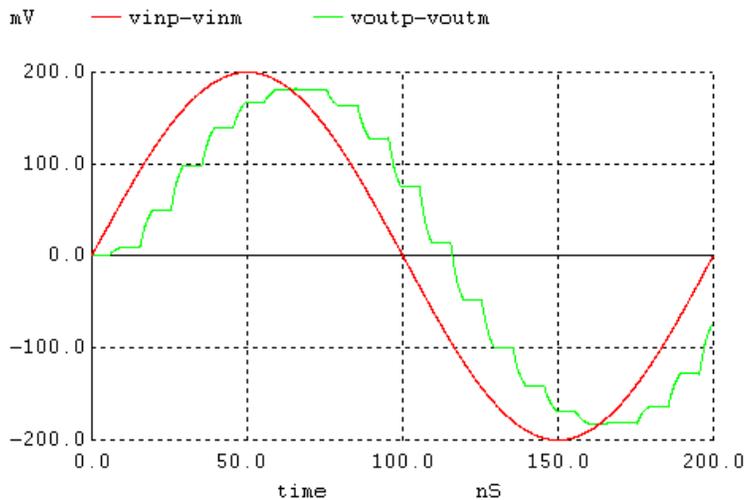
Suppose in Fig 25.19, that instead of the two input sine waves being connected to ground they are tied (together) to a common mode signal (say a noise voltage). Show, that a common mode signal (like a sine wave) won't change the circuits output signals. The amplitude of the common mode signal shouldn't be so large that the NMOS switches shut off.

Solution

When the two input sine waves in Fig 24.19 are tied together to a common mode signal (a noise signal of 5mV amplitude) instead of connecting them to ground the output signals won't change as seen in the simulations below.



Simulation with sine wave inputs connected to a common mode (noise) signal



Simulation with sine wave inputs connected to ground

*** Simulation for Figure 25.19

.control

destroy all

run

plot phi1+2.5 phi2+1.25 phi3

plot vinp-vinm voutp-voutm

.endc

.tran 100p 200n

.options scale=50n

* clock signals

Vphi1 phi1 0 DC 0 PULSE 1 0 5n 0 0 5n 10n

Vphi2 phi2 0 DC 0 PULSE 1 0 5.2n 0 0 5n 10n

Vphi3 phi3 0 DC 0 PULSE 0 1 5.4n 0 0 4n 10n

* input signals

vinp vinp vcom DC 0 SIN 500m 100m 5MEG

vinm vinm vcom DC 0 SIN 500m -100m 5MEG

vcom vcom 0 DC 0 SIN 5m 5m 5MEG

* op-amp model

E1 vop vcm vp vm 1e6

E2 vcm vom vp vm 1e6

Vcm vcm 0 DC 500m

* capacitors

Ct t1 vm 1p

Cb b1 vp 1p

Coutp voutp 0 1p

Coutm voutm 0 1p

* MOSFET switches

M1 vinp phi2 t1 0 NMOS L=1 W=10

M2 vinm phi2 b1 0 NMOS L=1 W=10

M3 t1 phi3 vop 0 NMOS L=1 W=10

M4 b1 phi3 vom 0 NMOS L=1 W=10

M5 vm phi1 vop 0 NMOS L=1 W=10

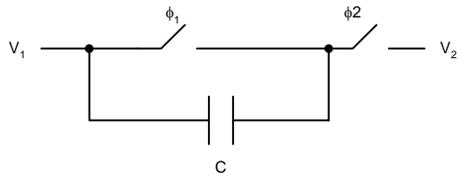
M6 vp phi1 vom 0 NMOS L=1 W=10

M7 vop phi3 voutp 0 NMOS L=1 W=10

M8 vom phi3 voutm 0 NMOS L=1 W=10

*50nm Spice models

25.6a) For the following diagram:



In the ϕ_1 phase:

$$q_1 = 0$$

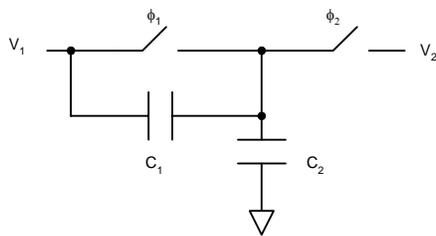
In the ϕ_2 phase

$$q_2 = (v_2 - v_1)C$$

Therefore:

$$I_{avg} = \frac{q_1 - q_2}{T} = \frac{(v_1 - v_2)C}{T} \Rightarrow R_{SC} = \frac{1}{C \cdot f_{clk}}$$

25.6b) For the following diagram:



In the ϕ_1 phase:

$$q_1 = v_1 C_2$$

In the ϕ_2 phase

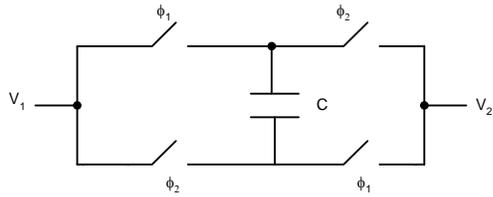
$$q_2 = (v_2 - v_1)C_1 + v_2 C_2$$

Therefore:

$$q_1 - q_2 = (C_1 + C_2)(v_1 - v_2)$$

$$I_{avg} = \frac{q_1 - q_2}{T} = \frac{(C_1 + C_2)(v_1 - v_2)}{T} \Rightarrow R_{SC} = \frac{1}{(C_1 + C_2) \cdot f_{clk}}$$

25.6c) For the following diagram:



Just prior to ϕ_1 closing the charge on C is equal to $(v_2 - v_1)$. After ϕ_1 closes, C is charged to $(v_1 - v_2)$. Therefore

$$q_1 = C(v_1 - v_2) - C(v_2 - v_1) = 2C(v_1 - v_2)$$

Similarly in the ϕ_2 phase

$$q_2 = C(v_2 - v_1) - C(v_1 - v_2) = 2C(v_2 - v_1)$$

$$I_{avg} = \frac{q_1 - q_2}{T} = \frac{4C(v_1 - v_2)}{T} \Rightarrow R_{SC} = \frac{1}{4C \cdot f_{clk}}$$

Problem 25.7

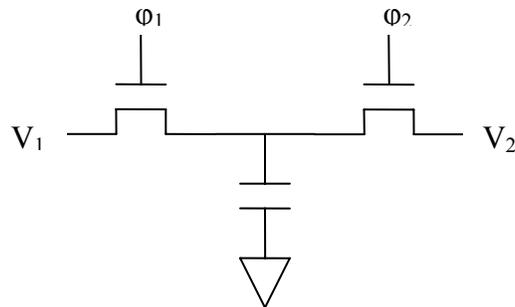


Figure 1

The switched-capacitor circuit seen in figure 1 can be used as a frequency-controlled resistor. The effective resistance of the circuit is given in *equation 25.18*

$$R_{sc} = 1/C * f_{clk}$$

For this circuit to work, the clocks need to be non-overlapping and their periods long enough for the capacitor to fully charge and discharge.

Figure 2 is a plot of the actual current through the circuit. In this simulation we have used following values.

- f_{clk} = 100 MHz. (non-overlapping)
- V_1 = 600 mV
- V_2 = 400 mV
- C = 100 fF

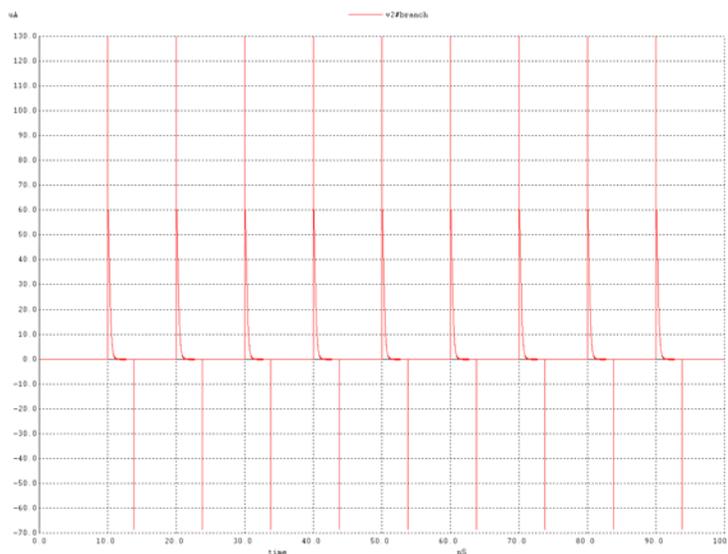


Figure 1 Actual current

If we take the mean of the actual current we get the plot below. ($I_{avg} = 1.96\mu A$)

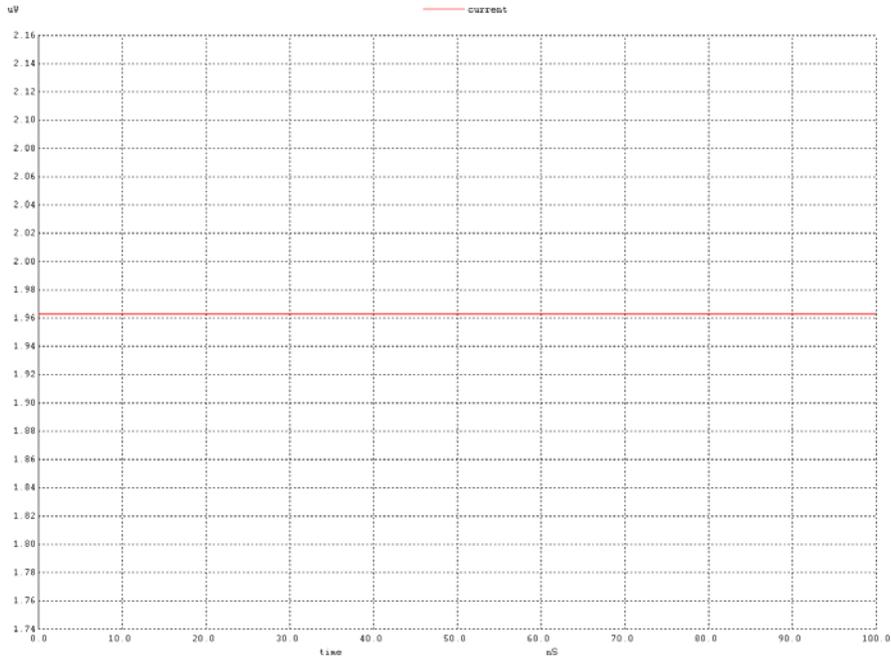


Figure 2 Mean current

Lets also look at what is happening with the voltage potential of the capacitor and the non-overlapping clocks(scaled-down).

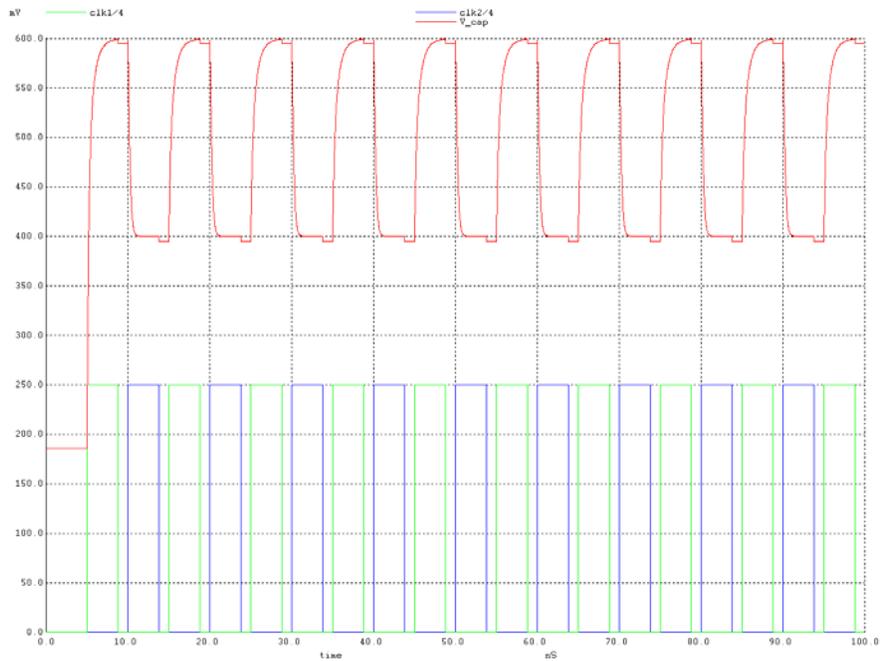


Figure 3 capacitor voltage and the non-overlapping clocks

If we calculate R_{sc} and the expected current we get,

$$R_{sc} = 1/(100\text{fF})(100\text{MHz}) = 100\text{k}\Omega, \text{ then,}$$

$$I = (V_1 - V_2)/R_{sc} = (.6-.4)/100\text{k} = 2 \mu\text{A}$$

This current value is very close to the simulation results. The difference in the values may be caused by clock feedthrough. In figure 3, if we look at the voltage on the capacitor when ϕ_1 goes low, we see it drop slightly.

The bottom plate of the capacitor should be connected to ground. This will avoid having the parasitic substrate capacitance from being in parallel with the switched capacitor. With the bottom plate connected to ground, both sides of the parasitic substrate capacitance are at ground.

The netlist:

```
problem 25.7
.control
destroy all
run
let current = unitvec(length(v2))*mean(v2#branch)
let V_cap = n1
plot V_cap clk1/4 clk2/4
plot current
.endc

.option scale=50n
.tran 10p 100n

vclk1 clk1 0 DC=0 pulse(0 1 5n 0 0 3.8n 10n)
vclk2 clk2 0 DC=0 pulse(0 1 10n 0 0 3.8n 10n)

V1 v1 0 DC=.6
V2 V2 0 DC=.4

M1 v1 clk1 n1 0 NMOS L=1 W=10
M2 v2 clk2 n1 0 NMOS L=1 W=10

C1 n1 0 100f

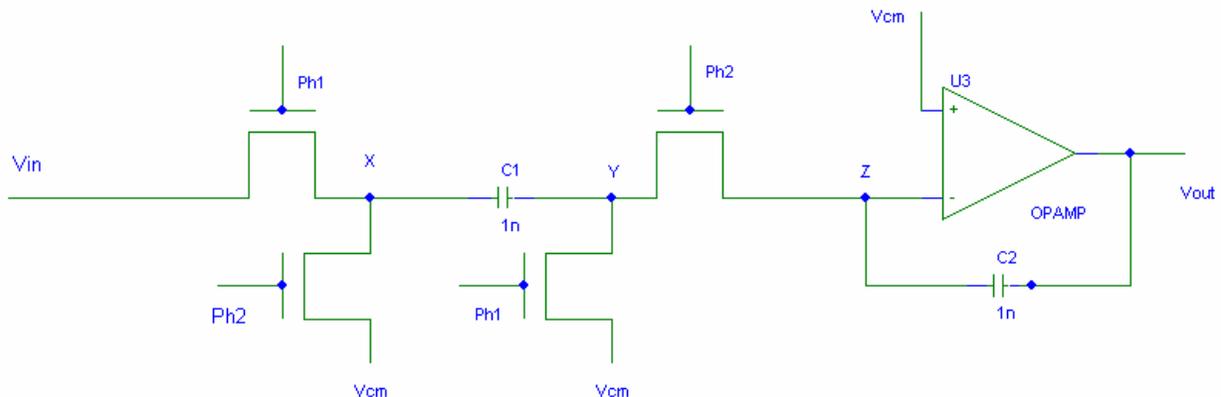
.include \50nm_models.txt
.end
```

Problem 25.8 Comment on the selection of bottom plate of C_f in the given figure:

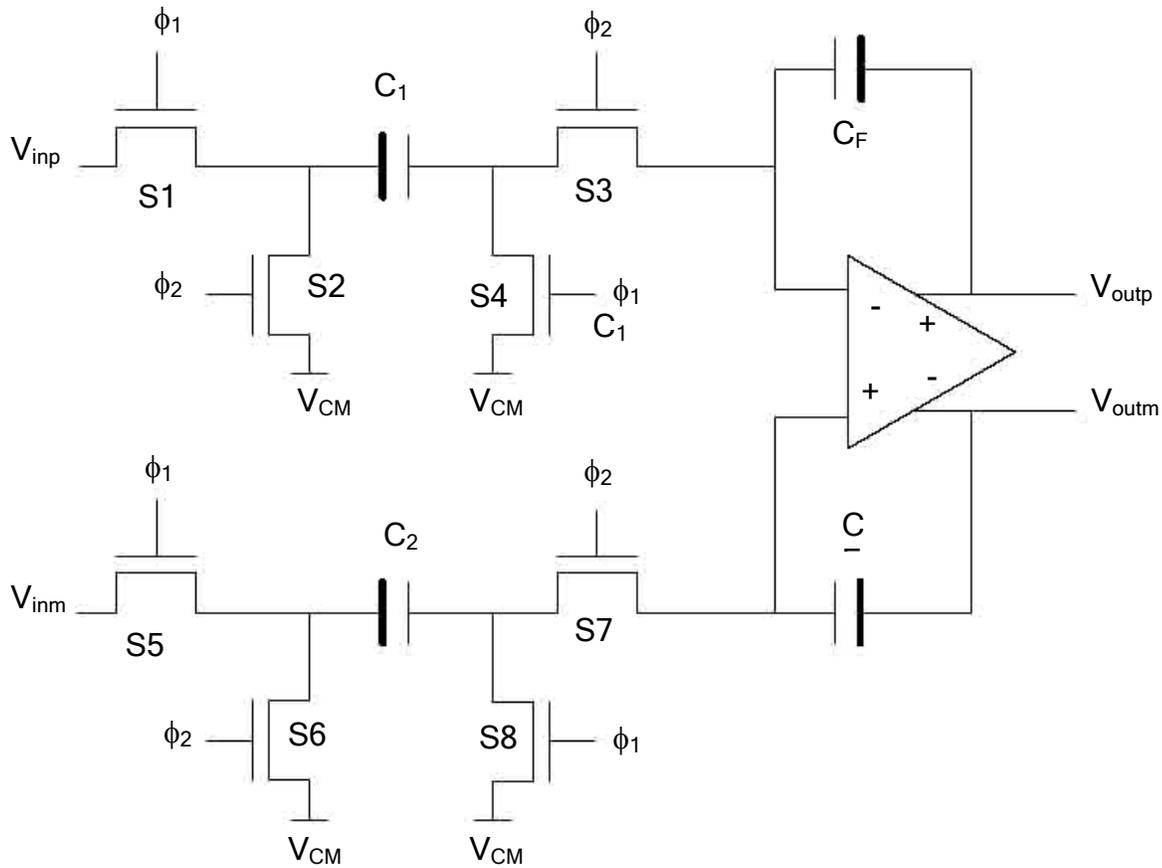
The bottom plate capacitor on the input capacitor is connected to X, as any change on the substrate voltage doesn't feed into the input of the opamp. Consider the case when Ph1 is ON, during this time any substrate noise doesn't feed to the top plate, but gets coupled on the i/p voltage source which is a low impedance node. On the other hand when Ph2 is ON and ph1 is off, the noise feeds on to the i/p voltage source V_{cm} and doesn't get coupled to the opamp i/p.

Now consider the case where the bottom plate is connected to node Y. Here when Ph1 is ON it doesn't affect the opamp input, but when Ph2 is ON it couples the substrate noise to the opamp input.

Moving to the capacitor on the feedback section. It is very obvious that we don't want any noise from the substrate to feed on to the i/p, to be amplified by the opamp. Which explains why we connect the bottom plate to the o/p node.



Problem 25.9



The transfer function is given by:

$$\frac{V_{outp} - V_{outm}}{V_{in} - V_{inm}} = \frac{V_{outp} - V_{outm}}{V_{CM}} = \left(\frac{1}{j\omega C_F} \right) \frac{1}{R_I}$$

where

$$R_I = \frac{1}{j\omega C_I f_{CLK}}$$

and f_{CLK} is the frequency of the clock signals ϕ_1 and ϕ_2 .

$$\frac{V_{out}}{V_{in}} = \frac{\left(\frac{1}{j\omega C_F} \right)}{\left(\frac{1}{j\omega C_I f_{CLK}} \right)} \Rightarrow \frac{1}{j\omega \left(\frac{C_F}{C_I} \frac{1}{f_{CLK}} \right)}$$

P25_10

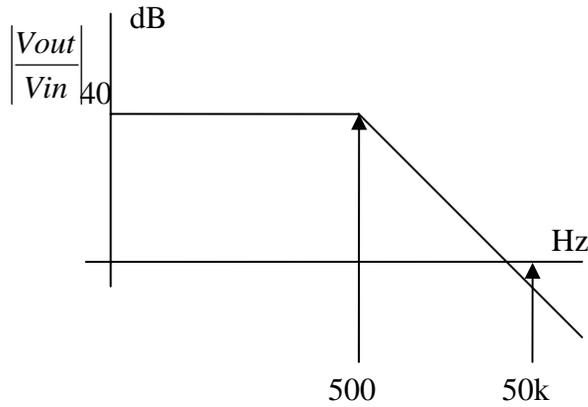


Figure 1.

The low frequency gain is:

$$20 * \log(\text{gain}) = 40 \Rightarrow \text{gain} = 10^2 = 100$$

$$\frac{C3}{C4} = 100$$

The pole and the zero are given by:

$$f_p = \frac{1}{2 * \pi * \left(\frac{C2}{C4} * \frac{1}{f_{clk}} \right)} = 500 \text{ and } f_z = \frac{1}{2 * \pi * \left(\frac{C1}{C3} * \frac{1}{f_{clk}} \right)} = 5000$$

Using $f_{clk}=100\text{kHz}$ and $C4=100\text{fF}$ $\implies C3=10\text{pF}$, $C2=3.2\text{pF}$ and $C1=.32\text{pF}$

Problem 25.11

The transfer function given by equation (25.29) is:

$$\frac{v_{out}(j\omega)}{v_{in}(j\omega)} = \frac{1}{j\omega \left(\frac{C_F}{C_I} \frac{1}{f_{CLK}} \right)} \left(\frac{\frac{\pi \cdot f}{f_{CLK}}}{\sin\left(\frac{\pi \cdot f}{f_{CLK}}\right)} e^{\frac{-j\omega f}{f_{CLK}}} \right)$$

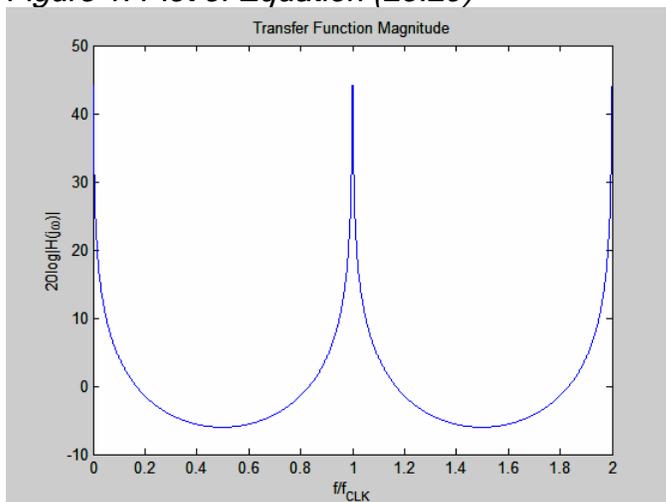
The magnitude of this function is:

$$\left| \frac{v_{out}(j\omega)}{v_{in}(j\omega)} \right| = \frac{1}{\omega \left(\frac{C_F}{C_I} \frac{1}{f_{CLK}} \right)} \frac{\frac{\pi \cdot f}{f_{CLK}}}{\sin\left(\frac{\pi \cdot f}{f_{CLK}}\right)}$$

If we normalize our function about $f_{CLK} = 1$, and let our capacitance ratio equal unity, we arrive at:

$$\left| \frac{v_{out}(j\omega)}{v_{in}(j\omega)} \right| = \frac{1}{2\pi \cdot f} \frac{\pi \cdot f}{\sin(\pi \cdot f)} = \frac{1}{2 \cdot \sin(\pi \cdot f)}$$

Figure 1: Plot of Equation (25.29)



Several observations can be made from Figure 1. The gain goes infinite at input frequencies of DC, f_{CLK} , $2f_{CLK}$, and so on. This makes sense, and this a characteristic of all digital filters. Basically, the space between DC and f_{CLK} is repeated indefinitely along the spectrum. The minimal gain occurs at half the sampling frequency, and that is represented as -6dB on the plot.

EE597 HW 25.12**Dong Pan**

25.12 For Fig 25.28, if C_i is 5pf and f_{clk} is 100Khz, estimate the Min. Slew rate requirements for the opamp providing V_{in}

$T=1/f = 10\mu$. We need to charge the C_i in half cycle.

For worst input condition, we need to charge the capacitor to VDD or GND, which the difference between the voltages of the cap is $\pm V_{DD}/2$.

$V = \text{input slewrate} * t$

Min input slew rate = $V/t = 0.5 / 5 \mu = 0.1 \text{ V/}\mu\text{s}$

Problem 25.13

Problem: Suppose the op-amp in problem 25.12 is used with a feedback factor of 0.5. Estimate the minimum unity gain frequency (f_{un}) that the op-amp must possess.

Solution:

The op-amp has to charge the C_I to the desired input voltage in half clock cycle. Thus the settling time of the op-amp, t_{set} , should be less than half of the clock period. i.e.,

$$t_{set} \leq \frac{1}{2f_{clk}}$$

The input voltage of the SC circuit, or the output voltage of the op-amp, can be estimated as (see Eq. 25.34 on page 853)

$$v_{in} = V_{in,final} (1 - e^{-t_{set}/\tau})$$

where $\tau = \frac{1}{2\pi f_{un}\beta}$ (Eq. 25.33 on page 853) is the close-loop time constant of the op-amp circuit.

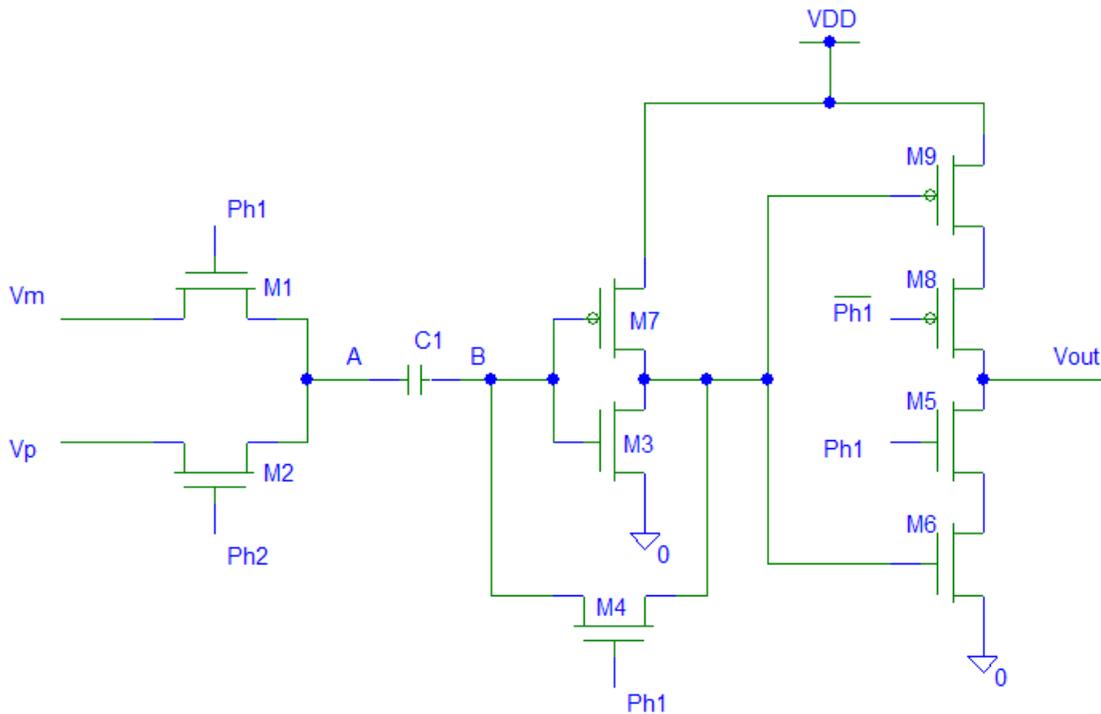
Assume v_{in} is required to settle to less than 1% of its final value, then

$$V_{in,final} (1 - e^{-t_{set}/\tau}) = V_{in,final} (1 - 1\%) \rightarrow t_{set} \approx 5\tau$$

Thus we have

$$5 \cdot \frac{1}{2\pi f_{un}\beta} \leq \frac{1}{2f_{clk}} \rightarrow f_{un} \geq \frac{5 \cdot f_{clk}}{\pi\beta} = \frac{5 \cdot 100 \text{ kHz}}{\pi \cdot 0.5} \approx 318.3 \text{ kHz}$$

Problem 25.14: Solution



*** PROBLEM 25.14 CMOS: Circuit Design, Layout, and Simulation ***

```
.control
destroy all
run
plot vp vm vout
.endc
.tran 100p 1u 0.1n
.options scale=50n
```

```
vp    vp    0    dc    0    pulse 0 1 0 1u
vm    vm    0    dc    0.5
VDD   VDD   0    DC    1
```

```
Vphi1 phi1 0    DC    0    PULSE 0    1 5.2n 0 0 5n 10n
Vphi2 phi2 0    DC    0    PULSE 1    0 5n 0 0 5n 10n
```

```
X1    vtout vb    vdd    inverter
Ca    va    vb    lp
Ma    vm    phi1  va    0    NMOS L=1 W=10
Mb    vp    phi2  va    0    NMOS L=1 W=10
Mc    vb    phi1  vtout 0    NMOS L=1 W=10
```

****output Latch*****

```
X1L   philbar phi1 vdd    inverter
M1PT  VDTP1  vtout VDD    VDD    PMOS L=1 W=20
M1PB  VOUT  PHI1BAR VDTP1 VDTP1 PMOS L=1 W=20
M1NT  VOUT  PHI1  VDTN1 VDTN1 NMOS L=1 W=10
M1NB  VDTN1 vtout 0    0    NMOS L=1 W=10
```

```
.subckt inverter vout    vin    vdd
M1    vout  vin    0    0    NMOS L=1 W=10
M2    vout  vin    vdd   vdd   PMOS L=1 W=20
.ends
```

